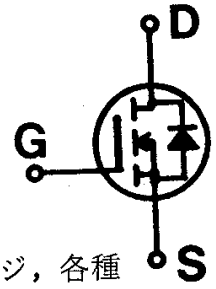
2SK352

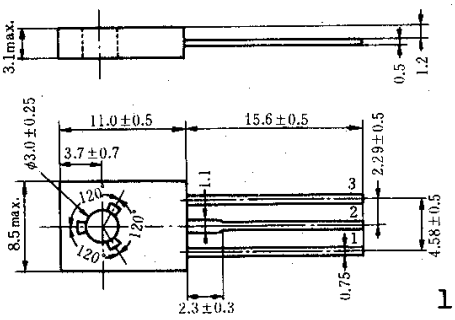
SILICON N-CHANNEL MOS FET

高速度電力スイッチング
高周波電力増幅



特　長

- ■高周波特性が優れている。
- ■入出力容量が低い。
- ■高精細ディスプレイのビデオ出力ステージ，各種用途のドライバ等に最適。



(Dimensions in mm)

(JEDEC TO-126 MOD.)

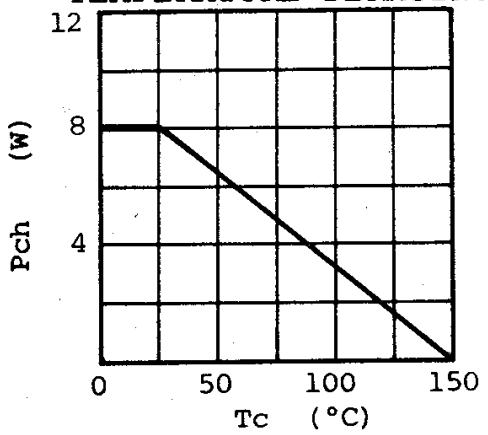
1. Source
2. Drain
3. Gate

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	250	V
Gate-Source Voltage	V_{GSS}	±9	V
Drain Current	I_D	0.3	A
Drain Peak Current	$I_{D(peak)}$	0.5	A
Body-Drain Diode Reverse Drain Current	I_{DR}	0.3	A
Channel Dissipation	Pch*	8	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55～+150	°C

*Value at Tc=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA , V_{GS}=0	250	-	-	V
Gate-Source Leak Current	I_{GSS}	V_{GS}=±9 V, V_{DS}=0	-	-	±1	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V, V_{GS}=0	-	-	1	mA
Gate-Source Cutoff Voltage	$V_{GS(off)}$	I_D=1mA , V_{DS}=10V	1.0	-	5.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	I_D=0.1A , V_{GS}=9V *	-	30	50	Ω
Drain-Source Saturation Voltage	$V_{DS(on)}$	I_D=0.1A , V_{GS}=9V *	-	3.0	5.0	V
Forward Transfer Admittance	|yfs|	I_D=0.15A, V_{DS}=20V *	50	80	-	mS
Input Capacitance	Ciss	V_{DS}=10 V, V_{GS}=0 f=1MHz	-	20	-	pF
Output Capacitance	Coss		-	10	-	pF
Reverse Transfer Capacitance	Crss		-	2.5	-	pF

*Pulse Test